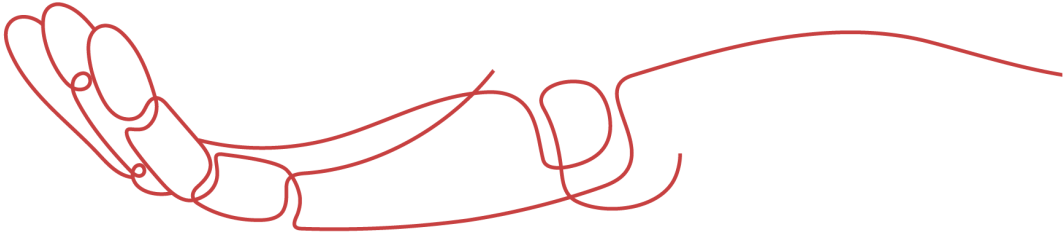




PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at



Datasheet



Resources



Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

General Description

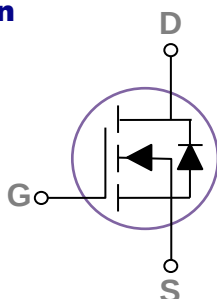
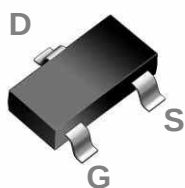
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
300V	2.7Ω	1.2A

Features

- 300V, 1.2A, $R_{DS(ON)} = 2.7\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching

SOT23-3 Pin Configuration



Applications

- Networking
- Load Switch
- LED applications

Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	300	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A = 25^\circ\text{C}$)	1.2	A
	Drain Current – Continuous ($T_A = 70^\circ\text{C}$)	0.4	A
I_{DM}	Drain Current – Pulsed ¹	2.0	A
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$)	0.5	W
	Power Dissipation – Derate above 25°C	0.012	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	40	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	300	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =300V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =240V , V _{GS} =0V , T _J =125°C	---	---	100	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =0.5A	---	2.7	4.0	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2	3	4	V

Dynamic and switching Characteristics

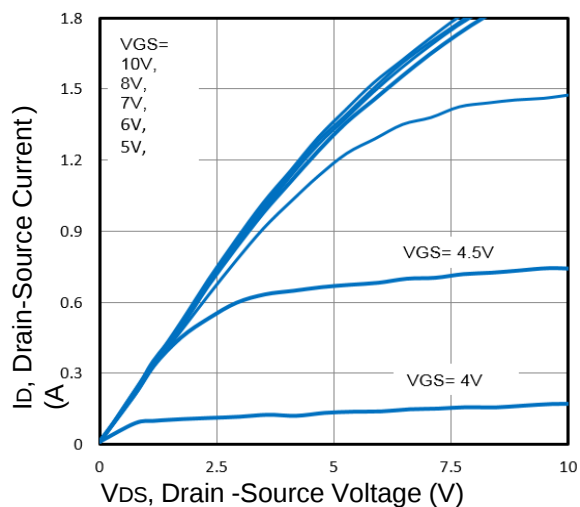
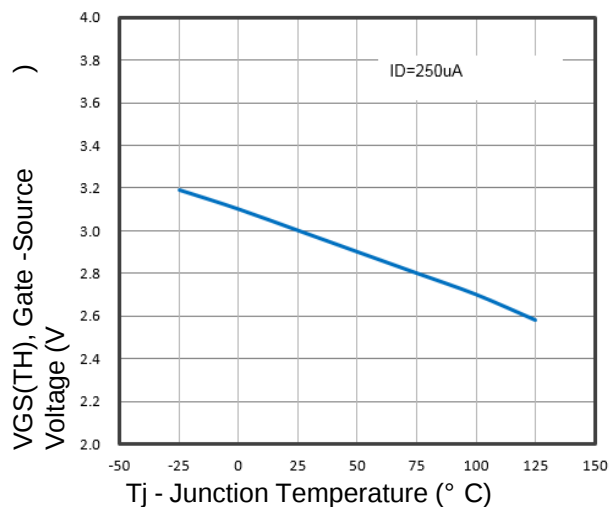
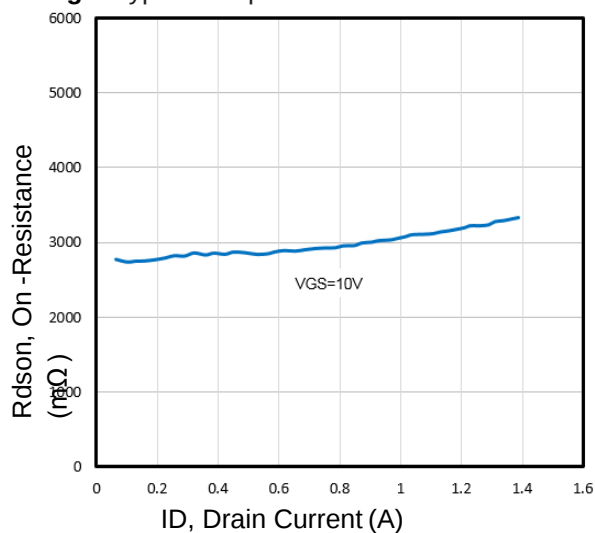
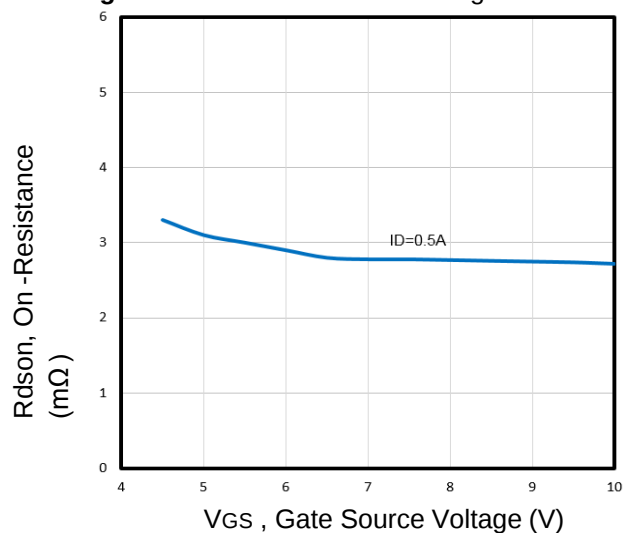
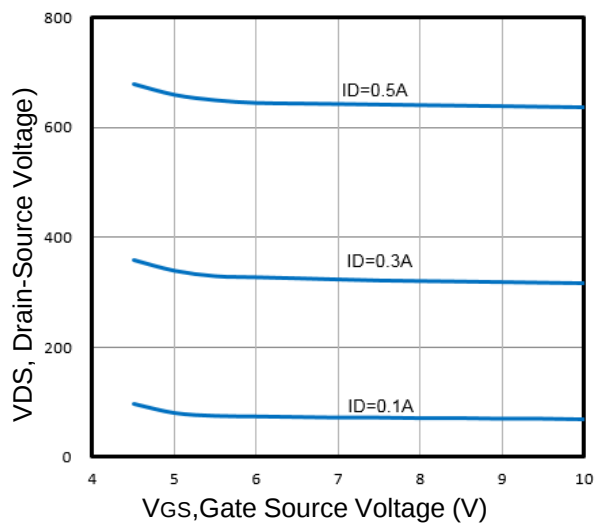
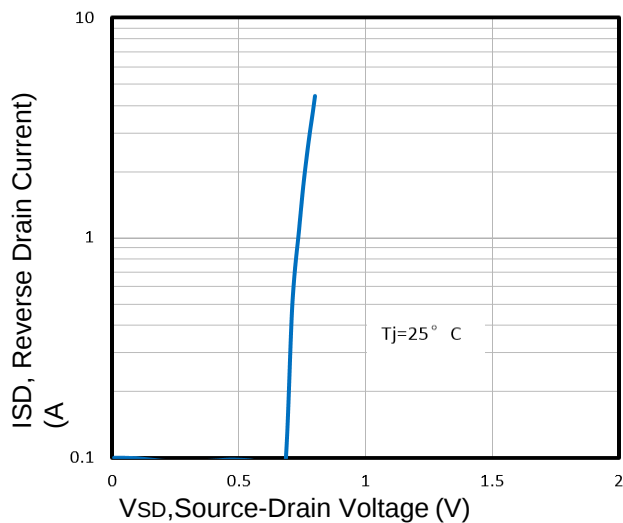
Q _g	Total Gate Charge ^{2, 3}	V _{DS} =150V , V _{GS} =10V , I _D =0.5A	---	2.5	---	nC
Q _{gs}	Gate-Source Charge ^{2, 3}		---	0.5	---	
Q _{gd}	Gate-Drain Charge ^{2, 3}		---	0.9	---	
T _{d(on)}	Turn-On Delay Time ^{2, 3}	V _{DD} =150V , V _{GS} =10V , R _G =3.3 I _D =0.5A	---	4.5	---	ns
T _r	Rise Time ^{2, 3}		---	6.0	---	
T _{d(off)}	Turn-Off Delay Time ^{2, 3}		---	19	---	
T _f	Fall Time ^{2, 3}		---	3.5	---	
C _{iss}	Input Capacitance	V _{DS} =150V , V _{GS} =0V , F=1MHz	---	35	---	pF
C _{oss}	Output Capacitance		---	3.2	---	
C _{rss}	Reverse Transfer Capacitance		---	0.1	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V , Force Current	---	---	1.2	A
I _{SM}	Pulsed Source Current		---	---	2.4	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =0.5A , T _J =25°C	---	---	1.3	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.


Fig1. Typical Output Characteristics

Fig2. Normalized Threshold Voltage Vs.

Fig3. On-Resistance vs. Drain Current and

Fig4. On-Resistance vs. Gate Source

Fig5. Drain-Source Voltage vs Gate-Source Voltage

Fig6. Typical Source-Drain Diode Forward Voltage

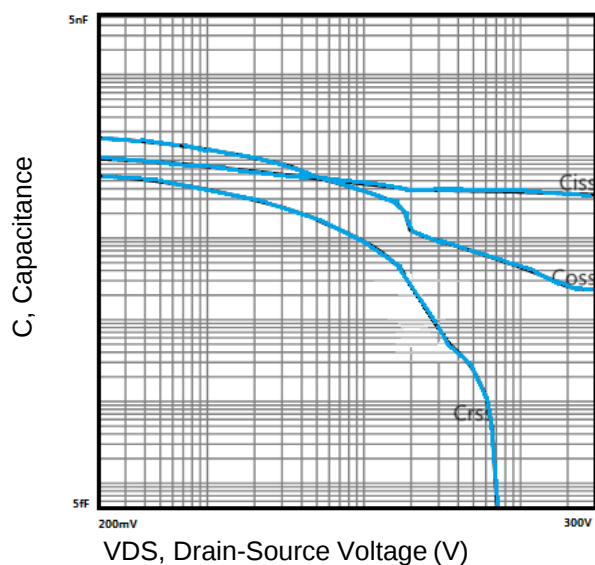


Fig7. Typical Capacitance Vs. Drain-Source Voltage

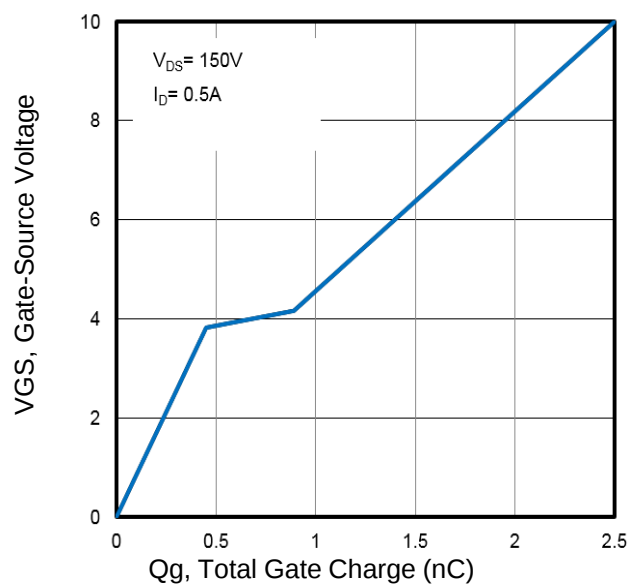
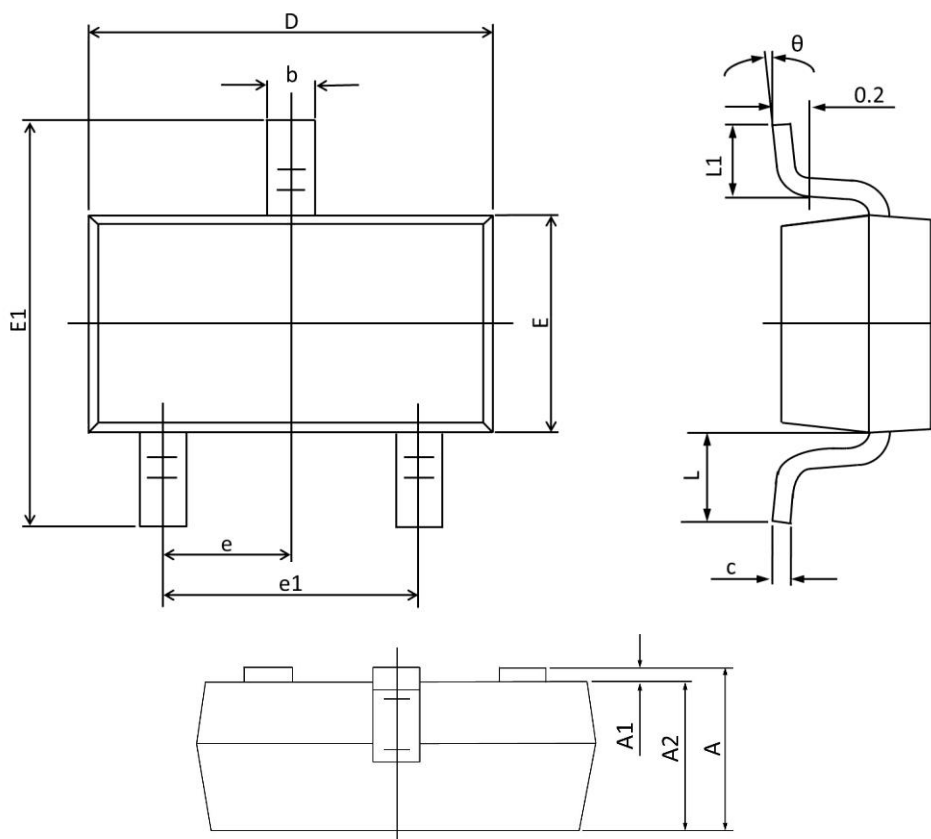


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

SOT23-3 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.450	0.041	0.057
A1	---	0.150	---	0.006
A2	0.900	1.300	0.035	0.051
b	0.300	0.490	0.012	0.019
c	0.100	0.200	0.004	0.008
D	2.820	3.050	0.111	0.120
E	1.500	1.750	0.059	0.069
E1	2.600	3.000	0.102	0.118
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.700 REF.		0.028 REF.	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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